A B S T R A C T

The invention relates to a method of forming a structure (30) provided with a layer (2) removed from a donor plate (10) comprising, prior to removal, a first $Si_{1-x}Ge_x$ layer (1) and a second layer (2) placed on the first layer formed of $Si_{1-y}Ge_y$ (1) (x, y respectively being in the range 0 to 1, and x being different from y), the method comprising the following steps:

a) implanting atomic species to form an embrittlement zone (4) beneath the second layer (2);

b) bonding the donor plate (10) to a receiving plate (20);

c) supplying energy to detach the removed layers (1', 2) from the donor plate (10) at the embrittlement zone (4);

d) rapid thermal annealing carried out at a temperature of about 1000°C or more for a period not exceeding 5 minutes;

e) selective etching of the remaining portion of the first layer (1') as opposed to the second layer (2).